

STM690A, STM692A, STM703 STM704, STM802, STM805, STM817/8/9

5V Supervisor with Battery Switchover

FEATURES SUMMARY

- 5V OPERATING VOLTAGE
- NVRAM SUPERVISOR FOR EXTERNAL LPSRAM
- CHIP-ENABLE GATING (STM818 only) FOR EXTERNAL LPSRAM (7ns max PROP DELAY)
- RST AND RST OUTPUTS
- 200ms (TYP) t_{rec}
- WATCHDOG TIMER 1.6sec (TYP)
- AUTOMATIC BATTERY SWITCHOVER
- LOW BATTERY SUPPLY CURRENT 0.4µA (TYP)
- POWER-FAIL COMPARATOR (PFI/PFO)
- LOW SUPPLY CURRENT 40µA (TYP)
- GUARANTEED \overline{RST} (RST) ASSERTION DOWN TO $V_{CC} = 1.0V$
- OPERATING TEMPERATURE:
 -40°C to 85°C (Industrial Grade)

Figure 1. Packages

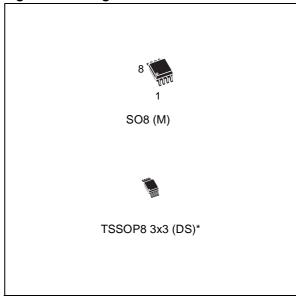


Table 1. Device Options

	Watchdog Input	Active- Low RST ⁽¹⁾	Active- High RST ⁽¹⁾	Manual Reset Input	Battery Switch- over	Power-fail Comparator	Chip- Enable Gating	Battery Freshness Seal
STM690A	~	V			~	'		
STM692A	~	~			~	'		
STM703		V		~	~	'		
STM704		V		~	~	'		
STM802L/M	~	~			~	'		
STM805L	~		~		~	~		
STM817L/M	~	V			~	~		~
STM818L/M	~	V			~		V	~
STM819L/M		V		~	~	'		~

Note: 1. All RST and RST outputs are push-pull.

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^{*} Contact local ST sales office for availability.

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STM690A/692A/703/704/802/805/817/818/819

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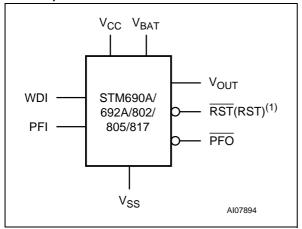
SUMMARY DESCRIPTION

The STM690A/692A/703/704/802/805/817/818/819 Supervisors are self-contained devices which provide microprocessor supervisory functions with the ability to non-volatize and write-protect external LPSRAM. A precision voltage reference and comparator monitors the V_{CC} input for an out-of-tolerance condition. When an invalid V_{CC} condition occurs, the reset output (RST) is forced low (or high in the case of RST). These devices also

offer a watchdog timer (except for STM703/704/819) as well as a power-fail comparator (except for STM818) to provide the system with an early warning of impending power failure.

These devices are available in a standard 8-pin SOIC package or a space-saving 8-pin TSSOP package.

Figure 2. Logic Diagram (STM690A/692A/802/805/817)



Note: 1. For STM805, reset output is active-high.

Figure 3. Logic Diagram (STM703/704/819)

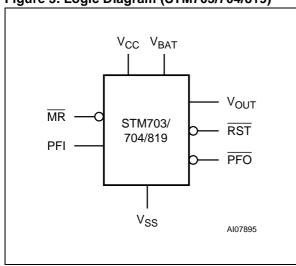


Figure 4. Logic Diagram (STM818)

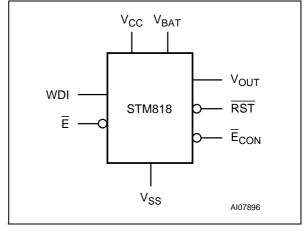
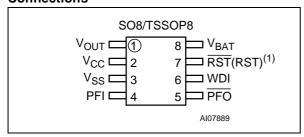


Table 2. Signal Names

MR	Push-button Reset Input
WDI	Watchdog Input
RST	Active-Low Reset Output
RST	Active-High Reset Output
Ē ⁽¹⁾	Chip Enable Input
E _{CON} ⁽¹⁾	Conditioned Chip Enable Output
Vout	Supply Voltage Output
V _{CC}	Supply Voltage
V _{BAT}	Back-up Supply Voltage
PFI	Power-fail Input
PFO	Power-fail Output
V _{SS}	Ground

Note: 1. STM818

Figure 5. STM690A/692A/802/805/817 Connections



Note: 1. For STM805, reset output is active-high.

Figure 6. STM703/704/819 Connections

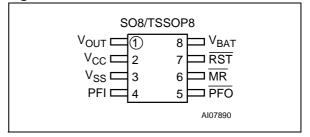
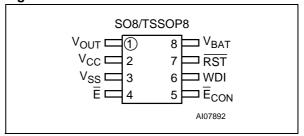


Figure 7. STM818 Connections



Pin Descriptions

MR. A logic low on /MR asserts the reset output. Reset remains asserted as long as MR is low and for trec after MR returns high. This active-low input has an internal pull-up. It can be driven from a TTL or CMOS logic line, or shorted to ground with a switch. Leave open if unused.

WDI. If WDI remains high or low for 1.6sec, the internal watchdog timer runs out and reset is triggered. The internal watchdog timer clears while reset is asserted or when WDI sees a rising or falling edge.

The watchdog function can be disabled by allowing the WDI pin to float.

 $\overline{\textbf{RST}}.$ Pulses low for t_{rec} when triggered, and stays low whenever V_{CC} is below the reset threshold or when $\overline{\textbf{MR}}$ is a logic low. It remains low for t_{rec} after either V_{CC} rises above the reset threshold, the watchdog triggers a reset, or $\overline{\textbf{MR}}$ goes from low to high.

RST. Pulses high for t_{rec} when triggered, and stays high whenever V_{CC} is above the reset threshold or when \overline{MR} is a logic high. It remains high for t_{rec} after either V_{CC} falls below the reset threshold, the watchdog triggers a reset, or \overline{MR} goes from high to low.

 $\textbf{V}_{\text{OUT}}.$ When V_{CC} is above the switchover voltage (VSO), VOUT is connected to VCC through a P-channel MOSFET switch. When VCC falls below VSO, VBAT connects to VOUT. Connect to VCC if no battery is used.

 V_{BAT} . When V_{CC} falls below V_{SO} , V_{OUT} switches from V_{CC} to V_{BAT} . When V_{CC} rises above V_{SO} + hysteresis, V_{OUT} reconnects to V_{CC} . V_{BAT} may exceed V_{CC} . Connect to V_{CC} if no battery is used.

E. The input to the chip-enable gating circuit. Connect to ground if unused.

 \overline{E}_{CON} . \overline{E}_{CON} goes low only when \overline{E} is low and reset is not asserted. If \overline{E}_{CON} is low when reset is asserted, \overline{E}_{CON} will remain low for 15 μ s or until \overline{E} goes high, whichever occurs first. In the disabled mode, \overline{E}_{CON} is pulled up to V_{OUT} .

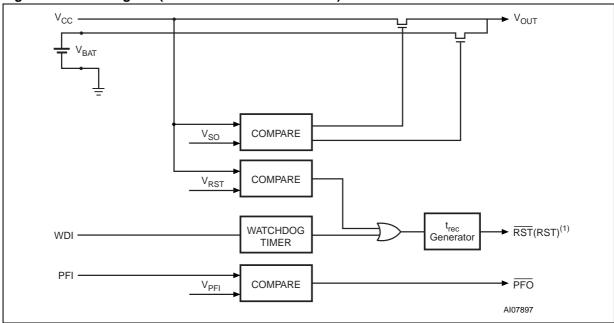
PFI. When PFI is less than V_{PFI} or when V_{CC} falls below 2.4V (or V_{SO}), \overline{PFO} goes low; otherwise, \overline{PFO} remains high. Connect to ground if unused.

PFO. When PFI is <u>less</u> than V_{PFI} , or V_{CC} falls <u>below</u> 2.4V (or V_{SO}), <u>PFO</u> goes low; otherwise, <u>PFO</u> remains high. Leave open if unused.

Table 3. Pin Description

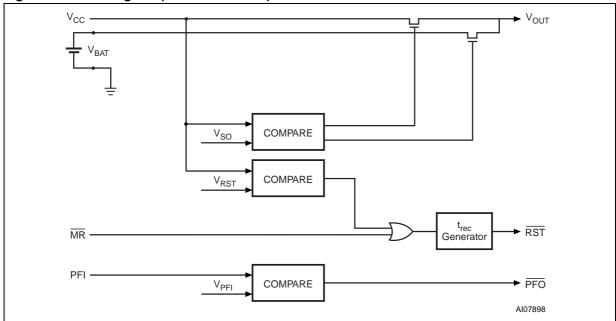
	Р	in		Name	Function
STM818	STM690A STM692A STM802 STM817	STM703 STM704 STM819	STM805		
_	_	6	_	MR	Push-button Reset Input
6	6	-	6	WDI	Watchdog Input
7	7	7	_	RST	Active-Low Reset Output
_	_	-	7	RST	Active-High Reset Output
1	1	1	1	V _{OUT}	Supply Output for External LPSRAM
2	2	2	2	V _{CC}	Supply Voltage
8	8	8	8	V_{BAT}	Backup-Battery Input
4	_	_	_	E	Chip Enable Input
5	_	_	_	ECON	Conditioned Chip Enable Output
_	4	4	4	PFI	PFI Power-fail Input
_	5	5	5	PFO	PFO Power-fail Output
3	3	3	3	V_{SS}	Ground

Figure 8. Block Diagram (STM690A/692A/802/805/817)



Note: 1. For STM805, reset output is active-high.

Figure 9. Block Diagram (STM703/704/819)



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Figure 10. Block Diagram (STM818)

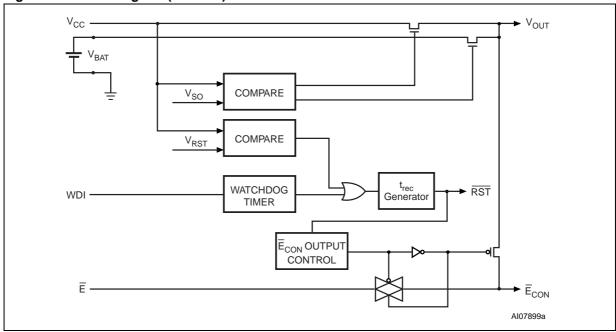
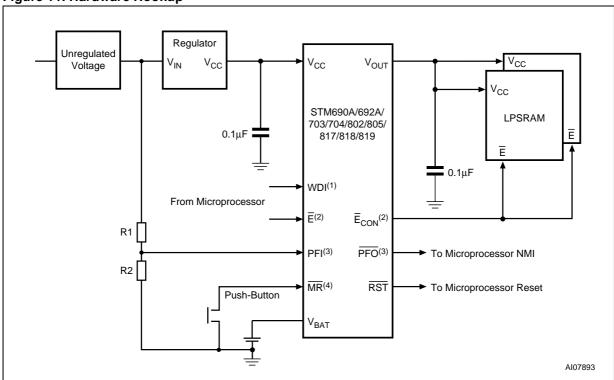


Figure 11. Hardware Hookup



Note: 1. For STM690A/692A/802/805/817/818.

- For STM818 only.
 Not available on STM818.
- 4. For STM703/704/819.

OPERATION

Reset Output

The STM690A/692A/703/704/802/805/817/818/819 Supervisor asserts a reset signal to the MCU whenever V_{CC} goes below the reset threshold (V_{RST}), a watchdog time-out occurs, or when the Push-button Reset Input (\overline{MR}) is taken low. \overline{RST} is guaranteed to be a logic low (logic high for STM805) for 0V < V_{CC} < V_{RST} if V_{BAT} is greater than 1V. Without a back-up battery, \overline{RST} is guaranteed valid down to V_{CC} =1V.

During power-up, once V_{CC} exc<u>eeds</u> the reset threshold an internal timer keeps \overline{RST} low fo<u>r the</u> reset time-out period, t_{rec} . After this interval \overline{RST} returns high.

If V_{CC} drops below the reset threshold, \overline{RST} goes low. Each time \overline{RST} is asserted, it stays low for at least the reset time-out period (t_{rec}). Any time V_{CC} goes below the reset threshold the internal timer clears. The reset timer starts when V_{CC} returns above the reset threshold.

Push-button Reset Input (STM703/704/819)

A logic low on \overline{MR} asserts reset. Reset remains asserted while \overline{MR} is low, and for t_{rec} (see Figure 38., page 24) after it returns high. The \overline{MR} input has an internal $40k\Omega$ pull-up resistor, allowing it to be left open if not used. This input can be driven with TTL/CMOS-logic levels or with open-drain/collector outputs. Connect a normally open momentary switch from \overline{MR} to GND to create a manual reset function; external debounce circuitry is

not required. If $\overline{\text{MR}}$ is driven from long cables or the device is used in a noisy environment, connect a 0.1 μ F capacitor from $\overline{\text{MR}}$ to GND to provide additional noise immunity. $\overline{\text{MR}}$ may float, or be tied to V_{CC} when not used.

Watchdog Input (NOT available on STM703/704/819)

The watchdog timer can be used to detect an out-of-control MCU. If the MCU does not toggle the Watchdog Input (WDI) within t_{WD} (1.6sec typ), the reset is asserted. The internal watchdog timer is cleared by either:

- 1. a reset pulse, or
- by toggling WDI (high-to-low or low-to-high), which can detect pulses as short as 50ns. If WDI is tied high or low, a reset pulse is triggered every 1.8sec (t_{WD} + t_{rec}).

The timer remains cleared and does not count for as long as reset is asserted. As soon as reset is released, the timer starts counting (see Figure 39., page 24).

Note: The watchdog function may be disabled by floating WDI or tri-stating the driver connected to WDI. When tri-stated or disconnected, the maximum allowable leakage current is 10uA and the maximum allowable load capacitance is 200pF.

Note: Input frequency greater than 20ns (50MHz) will be filtered.

Back-up Battery Switchover

In the event of a power failure, it may be necessary to preserve the contents of external SRAM through $V_{OUT}.$ With a backup battery installed with voltage $V_{BAT},$ the devices automatically switch the SRAM to the back-up supply when V_{CC} falls.

Note: If back-up battery is not used, connect both V_{BAT} and V_{OUT} to V_{CC} .

This family of Supervisors does not always connect V_{BAT} to V_{OUT} when V_{BAT} is greater than V_{CC} . V_{BAT} connects to V_{OUT} (through a 100Ω switch) when V_{CC} is below V_{RST} and V_{BAT} . This is done to allow the back-up battery (e.g., a 3.6V lithium cell) to have a higher voltage than V_{CC} .

Assuming V_{BAT} > 2.0V, switchover at V_{SO} ensures that battery back-up mode is entered before V_{OUT} gets too close to the 2.0V minimum required to reliably retain data in most external SRAMs. When V_{CC} recovers, hysteresis is used to avoid oscillation around the V_{SO} point. V_{OUT} is connected to V_{CC} through a 3 Ω PMOS power switch.

Note: The back-up battery may be removed while V_{CC} is valid, assuming V_{BAT} is adequately decoupled (0.1µF typ), without danger of triggering a reset.

Table 4. I/O Status in Battery Back-up

Pin	Status
V _{OUT}	Connected to V _{BAT} through internal switch
Vcc	Disconnected from V _{OUT}
PFI	Disabled
PFO	Logic low
Ē	High impedance
Econ	Logic high
WDI	Watchdog timer is disabled
WDO	Logic low
MR	Disabled
RST	Logic low
RST	Logic high
V _{BAT}	Connected to V _{OUT}

Chip-Enable Gating (STM818 only)

Internal gating of the chip enable (\overline{E}) signal prevents erroneous data from corrupting the external CMOS RAM in the event of an undervoltage condition. The STM818 uses a series transmission gate from \overline{E} to \overline{E}_{CON} (see Figure 12., page 11). During normal operation (reset not asserted), the \overline{E} transmission gate is enabled and passes all \overline{E} transitions. When reset is asserted, this path becomes disabled, preventing erroneous data from corrupting the CMOS RAM. The short \overline{E} propagation delay from \overline{E} to \overline{E}_{CON} enables the STM818 to be used with most $\mu Ps.$ If \overline{E} is low when reset asserts, \overline{E}_{CON} remains low for typically 15 μ s to permit the current WRITE cycle to complete. Connect \overline{E} to V_{SS} if unused.

Chip Enable Input (STM818 only)

The chip-enable transmission gate is disabled and \overline{E} is high impedance (disabled mode) while reset is asserted. During a power-down sequence when V_{CC} passes the reset threshold, the chip-enable transmission gate disables and \overline{E} immediately becomes high impedance if the voltage at \overline{E} is high. If \overline{E} is low when reset asserts, the chip-enable transmission gate will disable 15µs after reset asserts (see Figure 13., page 11). This permits the current WRITE cycle to complete during power-down.

Any time a reset is generated, the chip-enable transmission gate remains disabled and \overline{E} remains high impedance (regardless of \overline{E} activity) for the reset time-out period. When the chip enable transmission gate is enabled, the impedance of \overline{E} appears as a 40Ω resistor in series with the load at E_{CON}. The propagation delay through the chip-enable transmission gate depends on V_{CC}, the source impedance of the drive connected to E, and the loading on ECON. The chip enable propagation delay is production tested from the 50% point on E to the 50% point on \overline{E}_{CON} using a 50Ω driver and a 50pF load capacitance (see Figure 37., page 24). For minimum propagation delay, minimize the capacitive load at E_{CON} and use a low-output impedance driver.

Chip Enable Output (STM818 only)

When the chip-enable transmission gate is enabled, the impedance of \overline{E}_{CON} is equivalent to a 40Ω resistor in series with the source driving $\overline{E}.$ In the disabled mode, the transmission gate is off and an active pull-up connects \overline{E}_{CON} to V_{OUT} (see Figure 12., page 11). This pull-up turns off when the transmission gate is enabled.

Figure 12. Chip-Enable Gating

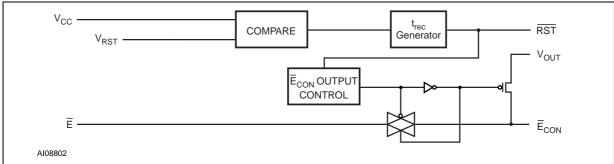
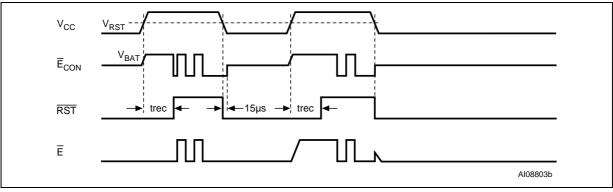


Figure 13. Chip Enable Waveform



Power-fail Input/Output (NOT available on STM818)

The Power-fail Input (PFI) is compared to an internal reference voltage (independent from the V_{RST} comparator). If PFI is less than the power-fail threshold (VPFI), the Power-Fail Output (PFO) will go low. This function is intended for use as an undervoltage detector to signal a failing power supply. Typically PFI is connected through an external voltage divider (see Figure 11., page 8) to either the unregulated DC input (if it is available) or the regulated output of the V_{CC} regulator. The voltage divider can be set up such that the voltage at PFI falls below V_{PFI} several milliseconds before the regulated V_{CC} input to the STM690A/692A/703/ 704/802/805/817/818/819 Supervisor or the microprocessor drops below the minimum operating voltage.

During battery back-up, the power-fail comparator turns off and PFO goes (or remains) low (see Figure 14 and Figure 15., page 13). This occurs after V_{CC} drops below 2.4V (or V_{SO}). When power returns, PFO is forced high (STM817/819 only), irrespective of V_{PFI} for the WRITE protect time (trec). At the end of this time, the power-fail comparator is enabled and PFO follows PFI. If the comparator is unused, PFI should be connected to \overline{V}_{SS} and \overline{V}_{SS} PFO left unconnected. PFO may be connected to \overline{V}_{SS} on the STM703/704/818 so that a low voltage on PFI will generate a reset output.

Applications Information

These Supervisor circuits are not short-circuit protected. Shorting V_{OUT} to ground - excluding power-up transients such as charging a decoupling capacitor - destroys the device. Decouple both V_{CC} and V_{BAT} pins to ground by placing $0.1\mu F$ capacitors as close to the device as possible.

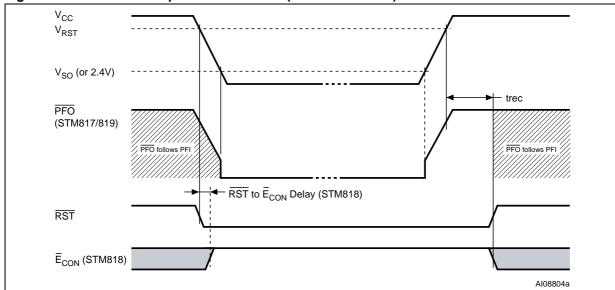


Figure 14. Power-fail Comparator Waveform (STM817/818/819)

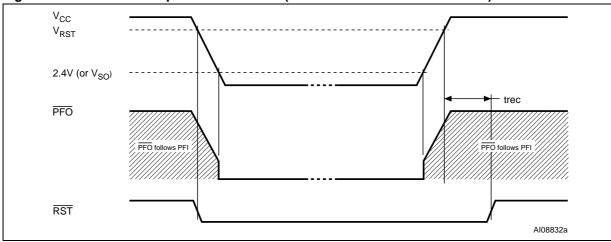


Figure 15. Power-fail Comparator Waveform (STM690A/692A/703/704/802/805)

Using a SuperCap[™] as a Backup Power Source

SuperCapsTM are capacitors with extremely high capacitance values (e.g., order of 0.47F) for their size. Figure 16 shows how to use a SuperCap as a back-up power source. The SuperCap may be connected through a diode to the 5V input. Since V_{BAT} can exceed V_{CC} while V_{CC} is above the reset threshold, there are no special precautions when using these supervisors with a SuperCap.

Negative-Going V_{CC} Transients

STM690A/692A/703/704/802/805/817/818/ 819 Supervisor are relatively immune to negative-Vcc transients (glitches). 34., page 22 shows typical transient duration versus reset comparator overdrive (for which the STM690A/692A/703/704/802/805/817/818/819 will NOT generate a reset pulse). The graph was generated using a negative pulse applied to V_{CC}, starting at V_{RST} + 0.3V and ending below the reset threshold by the magnitude indicated (comparator overdrive). The graph indicates the maximum pulse width a negative V_{CC} transient can have without causing a reset pulse. As the magnitude of the transient increases (further below the threshold), the maximum allowable pulse width decreases. Any combination of duration and overdrive which lies under the curve will NOT generate a reset signal. Typically, a V_{CC} transient that goes 100mV below the reset threshold and lasts 40µs or less will not cause a reset pulse. A 0.1µF bypass capacitor mounted as close as possible to the V_{CC} pin provides additional transient immunity.

Battery Freshness Seal (STM817/818/819)

The battery freshness seal disconnects the back-up battery from internal circuitry and V_{OUT} until it is needed. This allows an OEM to ensure that the back-up battery connected to V_{BAT} will be fresh when the final product is put to use. To enable the freshness seal:

- Connect a battery to V_{BAT};
- Ground PFO;
- Bring V_{CC} above the reset threshold and hold it there until reset is deasserted following the reset timeout period; and

4. Bring V_{CC} down again (Figure 17).

Use the same procedure for the STM818, but ground \overline{E}_{CON} instead of \overline{PFO} . Once the battery freshness seal is enabled (disconnecting the back-up battery from internal circuitry and anything connected to V_{OUT}), it remains enabled until V_{CC} is brought above V_{RST} .

Figure 16. Using a SuperCap™

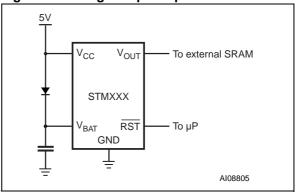
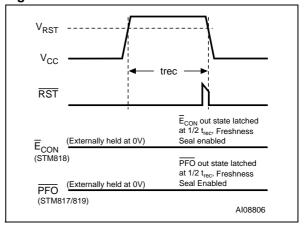


Figure 17. Freshness Seal Enable Waveform



TYPICAL OPERATING CHARACTERISTICS

Note: Typical values are at $T_A = 25$ °C

Figure 18. V_{BAT} -to- V_{OUT} On-Resistance vs. Temperature

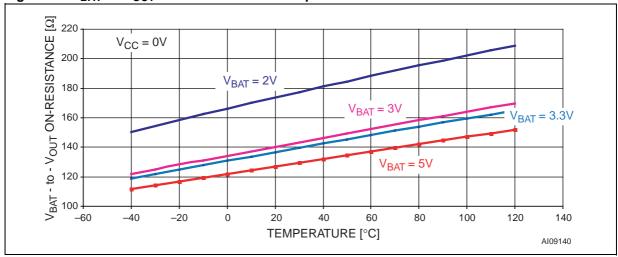


Figure 19. Supply Current vs. Temperature (no load)

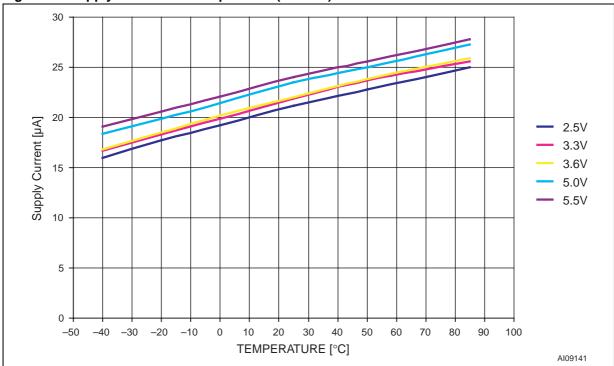


Figure 20. V_{PFI} Threshold vs. Temperature

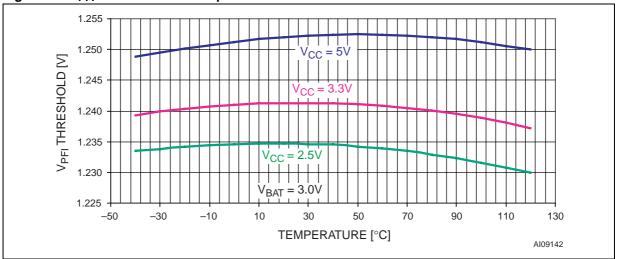


Figure 21. Reset Comparator Propagation Delay vs. Temperature

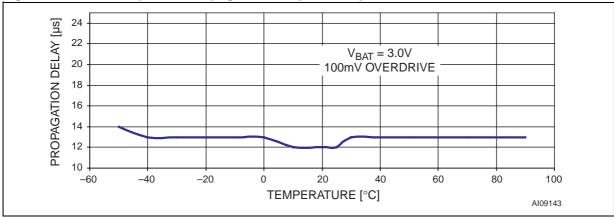
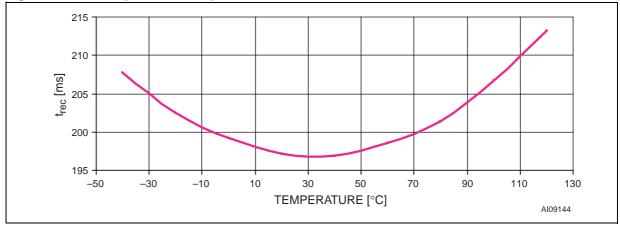


Figure 22. Power-up trec vs. Temperature





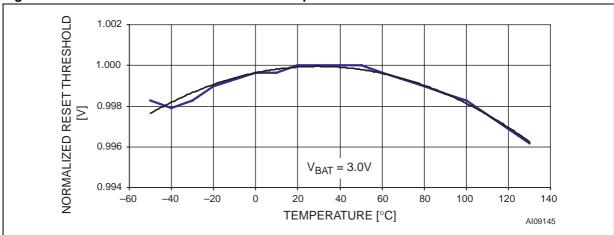


Figure 24. Watchdog Time-out Period vs. Temperature

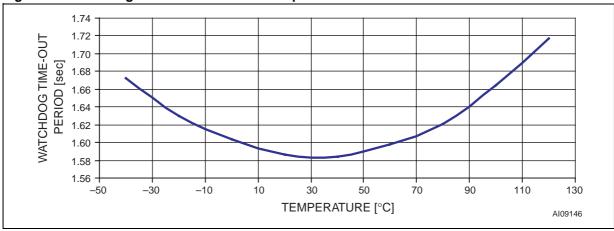


Figure 25. \overline{E} to \overline{E}_{CON} On-Resistance vs. Temperature

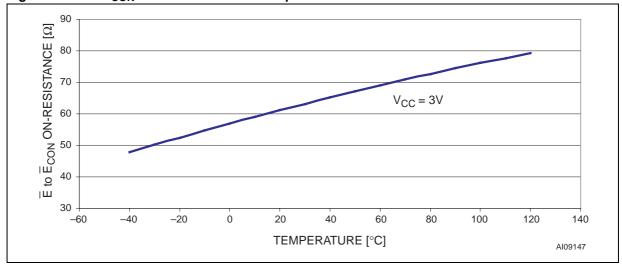


Figure 26. PFI to PFO Propagation Delay vs. Temperature

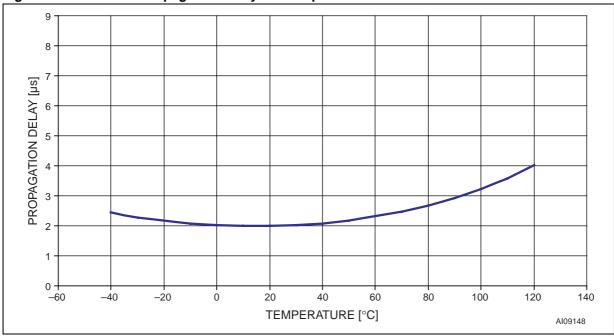
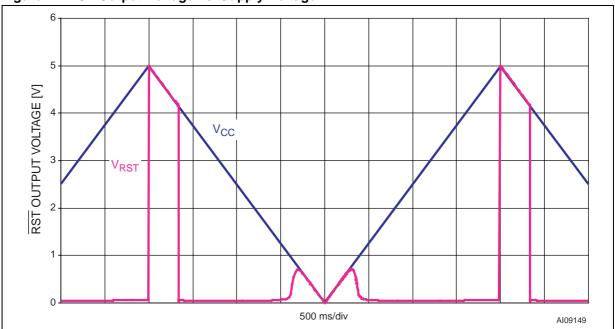
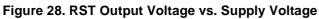


Figure 27. RST Output Voltage vs. Supply Voltage





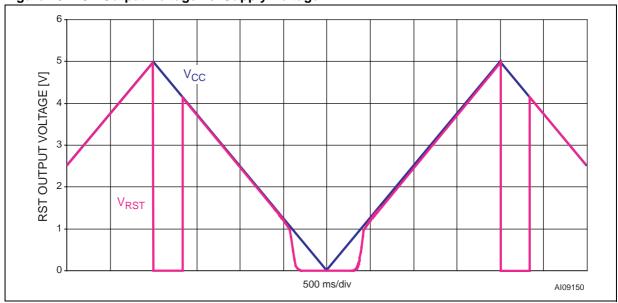


Figure 29. RST Response Time (Assertion)

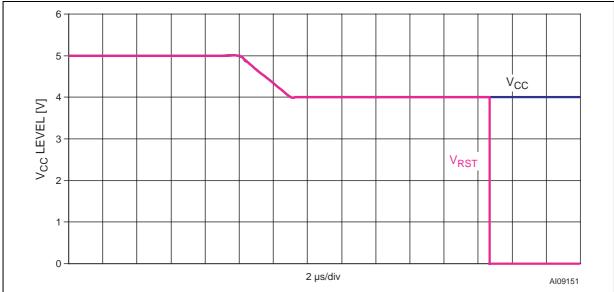


Figure 30. RST Response Time (Assertion)

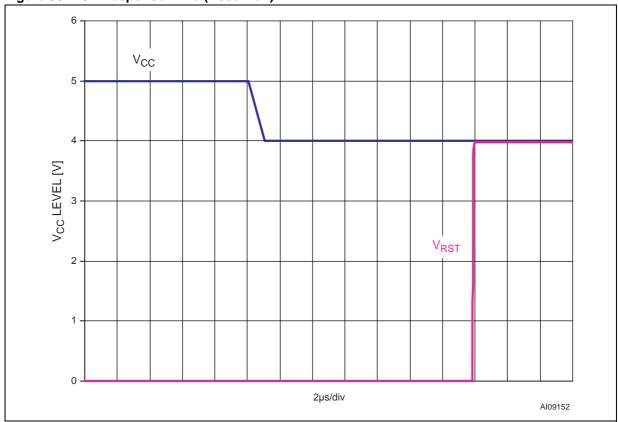


Figure 31. Power-fail Comparator Response Time (Assertion)

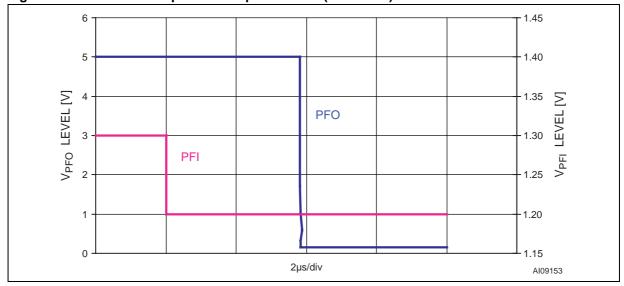


Figure 32. Power-fail Comparator Response Time (De-Assertion)

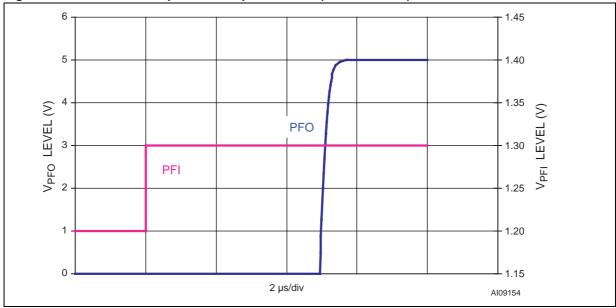


Figure 33. V_{CC} to Reset Propagation Delay vs. Temperature

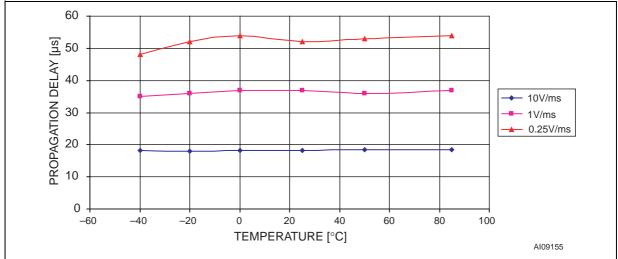


Figure 34. Maximum Transient Duration vs. Reset Threshold Overdrive

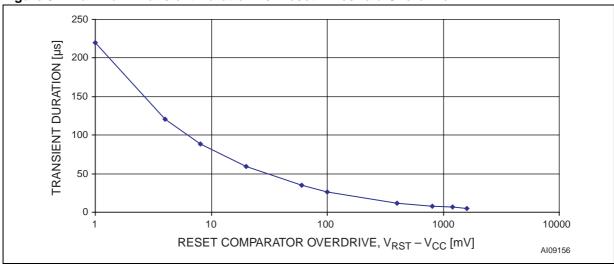
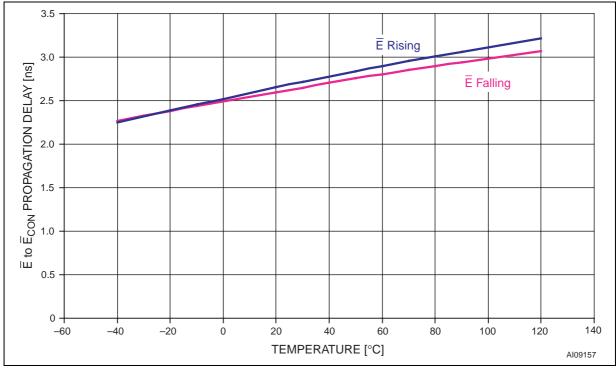


Figure 35. \overline{E} to \overline{E}_{CON} Propagation Delay vs. Temperature



MAXIMUM RATING

Stressing the device above the rating listed in the Absolute Maximum Ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not im-

plied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 5. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature (V _{CC} Off)	-55 to 150	°C
T _{SLD} ⁽¹⁾	Lead Solder Temperature for 10 seconds	260	°C
V _{IO}	Input or Output Voltage	-0.3 to V _{CC} +0.3	V
V _{CC} /V _{BAT}	Supply Voltage	-0.3 to 6.0	V
Io	Output Current	20	mA
P _D	Power Dissipation	320	mW

Note: 1. Reflow at peak temperature of 255°C to 260°C for < 30 seconds (total thermal budget not to exceed 180°C for between 90 to 150 seconds).

DC AND AC PARAMETERS

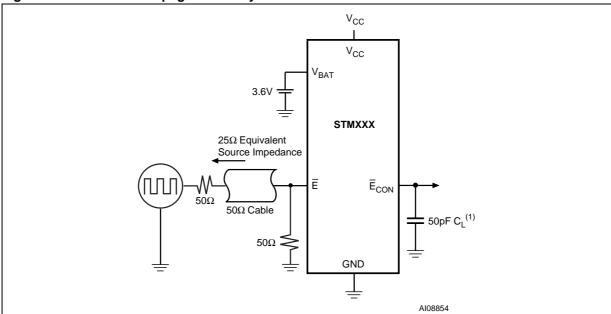
This section summarizes the operating measurement conditions, and the DC and AC characteristics of the device. The parameters in the DC and AC characteristics Tables that follow, are derived from tests performed under the Measurement

Conditions summarized in Table 6, Operating and AC Measurement Conditions. Designers should check that the operating conditions in their circuit match the operating conditions when relying on the quoted parameters.

Table 6. Operating and AC Measurement Conditions

Parameter	STM690A/692A/703/704/802/ 805/817/818/819	Unit
V _{CC} /V _{BAT} Supply Voltage	1.0 to 5.5	V
Ambient Operating Temperature (T _A)	-40 to 85	°C
Input Rise and Fall Times	≤ 5	ns
Input Pulse Voltages	0.2 to 0.8V _{CC}	V
Input and Output Timing Ref. Voltages	0.3 to 0.7V _{CC}	V

Figure 36. E to ECON Propagation Delay Test Circuit



Note: 1. C_L includes load capacitance and scope probe capacitance.

Figure 37. AC Testing Input/Output Waveforms

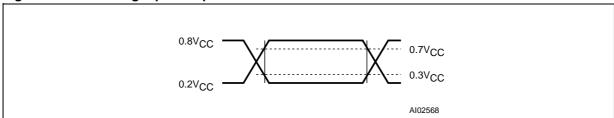
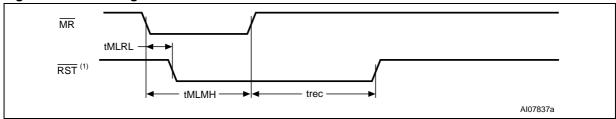


Figure 38. MR Timing Waveform



Note: 1. RST for STM805.

Figure 39. Watchdog Timing

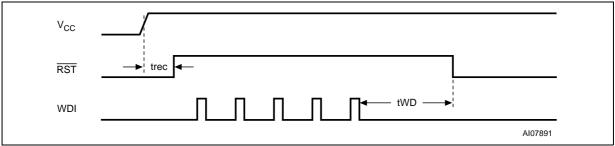


Table 7. DC and AC Characteristics

Sym	Alter- native	Description	Test Condition ⁽¹⁾	Min	Тур	Max	Unit
V _{CC} , V _{BAT} ⁽²⁾		Operating Voltage	$T_A = -40 \text{ to } +85^{\circ}\text{C}$	1.2 ⁽³⁾		5.5	V
		V _{CC} Supply Current	Excluding I _{OUT} (V _{CC} < 5.5V)		25	60	μA
Icc		V _{CC} Supply Current in Battery Back-up Mode	Excluding I_{OUT} ($V_{BAT} = 2.3V$, $V_{CC} = 2.0V$, $\overline{MR} = V_{CC}$)		25	35	μA
I _{BAT} ⁽⁴⁾		V _{BAT} Supply Current in Battery Back-up Mode	Excluding I _{OUT} (V _{BAT} = 3.6V)		0.4	1.0	μΑ
			I _{OUT1} = 5mA ⁽⁵⁾	V _{CC} – 0.03	V _{CC} – 0.015		٧
V _{OUT1}		V _{OUT} Voltage (Active)	I _{OUT1} = 75mA	V _{CC} - 0.3	V _{CC} – 0.15		٧
			$I_{OUT1} = 250 \mu A, V_{CC} > 2.5 V^{(5)}$	V _{CC} – 0.0015	V _{CC} – 0.0006		٧
V _{OUT2}		V _{OUT} Voltage (Battery	$I_{OUT2} = 250 \mu A, V_{BAT} = 2.3 V$	V _{BAT} – 0.1	V _{BAT} – 0.034		٧
V0012		Back-up)	$I_{OUT2} = 1$ mA, $V_{BAT} = 2.3$ V		V _{BAT} – 0.14		٧
	V _{CC} to \	V _{OUT} On-resistance			3	4	Ω
	V _{BAT} to	V _{OUT} On-resistance			100		Ω
		Input Leakage Current (MR)	4.5V < V _{CC} < 5.5V	75	125	300	μΑ
ILI		Input Leakage Current (PFI)	$0V = V_{IN} = V_{CC}$	-25	2	+25	nA
'LI	VCC to VBAT to	Input Leakage Current	WDI = V _{CC} , time average		120	160	μΑ
		(WDI) ⁽⁶⁾	WDI = GND, time average	<pre></pre>		μΑ	
V_{IH}		Input High Voltage (MR)	4.5V < V _{CC} < 5.5V	2.0			V
V_{IH}		Input High Voltage (WDI)	V_{RST} (max) < V_{CC} < 5.5 V	0.7V _{CC}			V
V_{IL}		Input Low Voltage (MR)	$4.5V < V_{CC} < 5.5V$			8.0	V
V _{IL}		Input Low Voltage (WDI)	V _{RST} (max) < V _{CC} < 5.5V			0.3V _{CC}	V
\/		Output Low Voltage (PFO, RST, RST)	$V_{CC} = V_{RST}$ (max), $I_{SINK} = 3.2$ mA			0.3	V
V _{OL}		Output Low Voltage (E _{CON})	$V_{CC} = V_{RST} \text{ (max)},$ $I_{OUT} = 1.6\text{mA}, \overline{E} = 0\text{V}$			0.2V _{CC}	V
Ve		Output Low Veltors (DCT)	$I_{SINK} = 50 \mu A; V_{CC} = 1.0 V; V_{BAT} = V_{CC}; T_A = 0 ^{\circ}C to 85 ^{\circ}C$			0.3	٧
V _{OL}		Output Low Voltage (RST)	I_{SINK} = 100µA; V_{CC} = 1.2V; $V_{BAT} = V_{CC}$			0.3	V

STM690A/692A/703/704/802/805/817/818/819

Sym	Alter- native	Description	Test Condition ⁽¹⁾		Min	Тур	Max	Unit
RST)		Output High Voltage (RST, RST)		E = 1mA, RST (max)	2.4			V
		Output High Voltage (\overline{E}_{CON})		_{RST} (max), mA, E = V _{CC}	0.8V _{CC}			V
		Output High Voltage (PFO)		E = 75μA, _{RST} (max)	0.8V _{CC}			٧
V _{OH}		Output High Voltage		$IA; V_{CC} = 1.1V;$ $I_A = 0^{\circ}C \text{ to } 85^{\circ}C$			0.8	V
VOH		Output Flight Voltage		$V_{CC} = 1.2V;$ $V_{CC} = V_{CC}$			0.9	V
V _{OHB}		V _{OH} Battery Back-up (\overline{E}_{CON} , RST, RST)	I _{SOURCE}	0.8V _{BAT}			V	
Power-fa	ail Compa	arator (NOT available on STM	818)					
V _{PFI}		PFI Input Threshold	PFI Falling	All other versions	1.20	1.25	1.30	V
			$(V_{CC} = 5V)$	STM802	1.225	1.250	1.275	V
t _{PFD}		PFI to PFO Propagation Delay				2		μs
I _{SC}		PFO Output Short to GND Current	V _{CC} = 5V	, V _{PFO} = 0V	0.1	0.75	2.0	mA
Battery	Switchov	er						
			Power-down	V _{RST} > V _{BAT}		V _{BAT}		V
		Battery Back-up	Power-down	V _{RST} < V _{BAT}		V _{RST}		V
V_{SO}		Switchover Voltage ^(7,8) (V _{CC} < V _{BAT} & V _{CC} < V _{RST})	Dawarus	V _{RST} > V _{BAT}		V_{BAT}		V
			Power-up	V _{RST} < V _{BAT}		V _{RST}		V
		Hysteresis				40		mV
Reset Th	nresholds	S						
\/ _E ==		Reset Threshold ⁽⁹⁾	STM690A/7	03, STM8XXL	4.50	4.65	4.75	V
V _{RST}		Reset Inresnoid(9)	STM692A/704, STM8XXM		4.25	4.40	4.50	V
		Reset Threshold Hysteresis				25		mV
		V _{CC} to RST Delay (from V _{RST} , V _{CC} falling at 10V/ms)	STM81	7/818/819		100		μs
t _{rec}		RST Pulse Width			140	200	280	ms
	1	l .	I		1			1

Sym	Alter- native	Description	Test Condition ⁽¹⁾	Min	Тур	Max	Unit
Push-bu	tton Res	et Input (STM703/704/819)					
t	tur	MR Pulse Width	STM703/704	150			ns
t _{MLMH}	t _{MR}	WIR Pulse Width	STM819	1			μs
t. - .	t	MR to RST Output Delay	STM703/704			250	ns
t _{MLRL}	t _{MRD}	WR to RST Output Delay	STM819		120		ns
		MR Glitch Immunity	STM819		100		ns
		MR Pull-up Resistor	$\overline{MR} = 0V; V_{CC} = 5V$	45	63	85	kΩ
Watchdo	g Timer	(NOT available on STM703/70	04/819)			•	
	t _{WD}	Watchdog Timeout Period	V _{RST} (max) < V _{CC} < 5.5V	1.12	1.60	2.24	s
		WDI Pulse Width	V _{RST} (max) < V _{CC} < 5.5V 50				ns
Chip-En	able Gati	ng (STM818 only)					
	E-to-	CON Resistance	V _{CC} = V _{RST} (max)		40	150	Ω
E-to-E _{CON} Propagation Delay			4.5V < V _{CC} < 5.5V		2	7	ns
Reset-to-E _{CON} High Delay			(Power-down)		15		μs
	E _{CON} S	hort Circuit Current	Vcc = 5V Disable Mode		0.75	2.0	mA

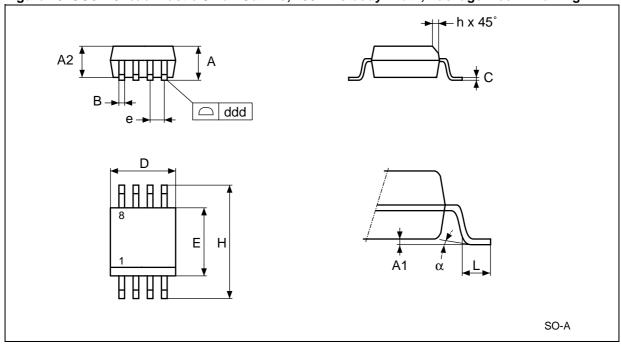
Note: 1. Valid for Ambient Operating Temperature: TA = -40 to 85°C; VCC = 4.75V to 5.5V for "L" versions; VCC = 4.5V to 5.5V for "M" versions; VCC = 4.5V to 5.5V for "L" versions; VCC = 4.5V to 5.5V for "M" versions; VCC = 4.5V to 5.5V for "L" versions; VCC = 4.5V to 5.5V for "M" versions; VCC = 4.5V to 5.5V for "L" versions; VCC = 4.5V to 5.5V for "M" versions; VCC = 4.5V to 5. sions; and $V_{BAT} = 2.8V$ (except where noted).

- 3. V_{CC} (min) = 1.0V for T_A = 0°C to +85°C. 4. Tested at V_{BAT} = 3.6V, V_{CC} = 3.5V and 0V.
- 5. Guaranteed by design.
- 6. WDI input is designed to be driven by a three-state output device. To float WDI, the "high impedance mode" of the output device must have a maximum leakage current of 10µA and a maximum output capacitance of 200pF. The output device must also be able to source and sink at least 200µA when active.
- 7. When $V_{BAT} > V_{CC} > V_{RST}$, V_{OUT} remains connected to V_{CC} until V_{CC} drops below V_{RST} . 8. When $V_{RST} > V_{CC} > V_{BAT}$, V_{OUT} remains connected to V_{CC} until V_{CC} drops below the battery voltage $(V_{BAT}) 75$ mV.
- 9. For V_{CC} falling.

^{2.} V_{CC} supply current, logic input leakage, Watchdog functionality, Push-button Reset functionality, PFI functionality, state of RST and RST tested at V_{BAT} = 3.6V, and V_{CC} = 5.5V. The state of RST or RST and PFO is tested at V_{CC} = V_{CC} (min). Either V_{CC} or V_{BAT} can go to 0V if the object is greater than 2.0V.

PACKAGE MECHANICAL

Figure 40. SO8 - 8-lead Plastic Small Outline, 150 mils body width, Package Mech. Drawing



Note: Drawing is not to scale.

Table 8. SO8 – 8-lead Plastic Small Outline, 150 mils body width, Package Mechanical Data

Symb		mm		inches			
Зушь	Тур	Min	Max	Тур	Min	Max	
А	-	1.35	1.75	_	0.053	0.069	
A1	-	0.10	0.25	_	0.004	0.010	
В	-	0.33	0.51	_	0.013	0.020	
С	-	0.19	0.25	_	0.007	0.010	
D	-	4.80	5.00	_	0.189	0.197	
ddd	-	-	0.10	_	_	0.004	
E	-	3.80	4.00	_	0.150	0.157	
е	1.27	_	-	0.050	-	-	
Н	-	5.80	6.20	_	0.228	0.244	
h	-	0.25	0.50	_	0.010	0.020	
L	-	0.40	0.90	_	0.016	0.035	
α	-	0°	8°	-	0°	8°	
N		8			8		

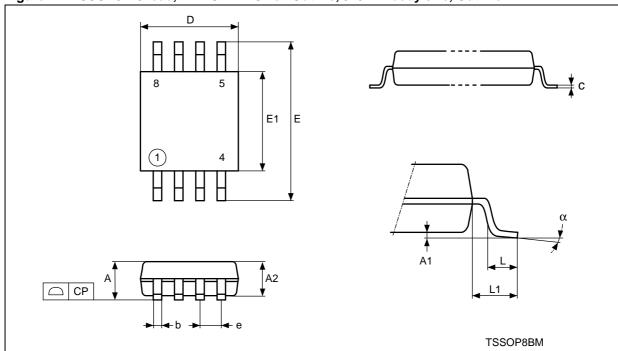


Figure 41. TSSOP8 – 8-lead, Thin Shrink Small Outline, 3x3mm body size, Outline

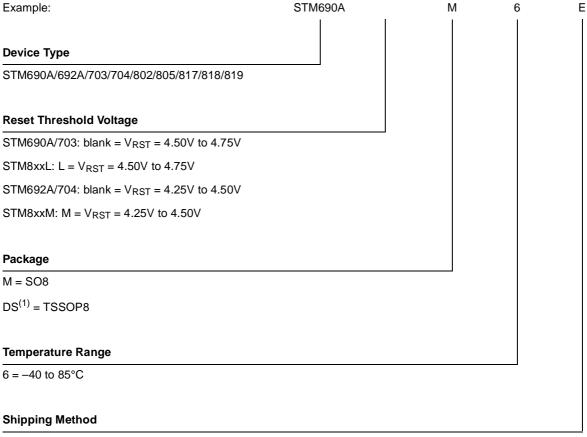
Note: Drawing is not to scale.

Table 9. TSSOP8 – 8-lead, Thin Shrink Small Outline, 3x3mm body size, Mechanical Data

Symb	mm			inches		
	Тур	Min	Max	Тур	Min	Max
А	_	-	1.10	-	_	0.043
A1	_	0.05	0.15	_	0.002	0.006
A2	0.85	0.75	0.95	0.034	0.030	0.037
b	_	0.25	0.40	_	0.010	0.016
С	_	0.13	0.23	_	0.005	0.009
СР	_	_	0.10	_	_	0.004
D	3.00	2.90	3.10	0.118	0.114	0.122
е	0.65	-	_	0.026	_	_
E	4.90	4.65	5.15	0.193	0.183	0.203
E1	3.00	2.90	3.10	0.118	0.114	0.122
L	0.55	0.40	0.70	0.022	0.016	0.030
L1	0.95	-	-	0.037	-	-
α	-	0°	6°	-	0°	6°
N	8			8		

PART NUMBERING





E = Tubes (Pb-Free - ECO PACK®)

F = Tape & Reel (Pb-Free - ECO PACK®)

Note: 1. Contact local ST sales office for availability.

For other options, or for more information on any aspect of this device, please contact the ST Sales Office nearest you.

Table 11. Marking Description

Part Number	Reset Threshold	Package	Topside Marking	
STM690A	4.65V	SO8	690A	
STM692A	4.65V	SO8	692A	
STM703	4.65V	SO8	703	
STM704	4.40V	SO8	704	
STM802L	4.65V	SO8	802L	
STM802M	4.40V	SO8	802M	
STM805L	4.65V	SO8	805L	
CTM047I	4.65\/	SO8	817L	
STM817L	4.65V	TSSOP8		
CTM047M	4.40\/	SO8	817M	
STM817M	4.40V	TSSOP8		
STM818L	4.65V	SO8	0401	
STIVISTOL	4.05 V	TSSOP8	818L	
STM818M	4.40V	SO8	818M	
211/101/01/01	4.40 V	TSSOP8		
CTM940I	4.05\/	SO8	819L	
STM819L	4.65V	TSSOP8		
STM910M	4.40\/	SO8	819M	
STM819M	4.40V	TSSOP8		

REVISION HISTORY

Table 12. Document Revision History

Date	Version	Revision Details	
October 2003	1.0	First Issue	
31-Oct-03	1.1	Update DC Characteristics (Table 7)	
22-Dec-03	2.0	Reformatted; updated characteristics (Figure 1, 3, 4, 7, 8, 9, 10, 11, 12, 13, 14, 15, 17; Table 3, 4, 7, 9, 11)	
16-Jan-04	2.1	Add Typical Characteristics (Figure 18, 19, 20, 21, 22, 23, 24, 25, 26, 27, 28, 29, 30, 31, 32, 33, 34, 35)	
08-Apr-04	2.2	Update characteristics (Figure 13, 21, 26, 28, 29, 30, 33, 34; Table 1,7)	
25-May-04	3.0	Remove references to 'Open Drain' (Figure 2, 5, 8; Table 2); update characteristics (Table 3, 7)	
05-Jul-04	4.0	Update package availability, pin description; promote document (Figure 1, 14, 15; Table 3. 7, 10)	
29-Sep-04	5.0	Clarify root part numbers, pin descriptions (Figure 11, 13, 36; Table 7, 10)	

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